

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ge, et al. Docket No.: TSM03-0660
Serial No.: 10/699,574 Art Unit: TBD
Filed: October 31, 2003 Examiner: TBD
For: Strained Silicon Structure

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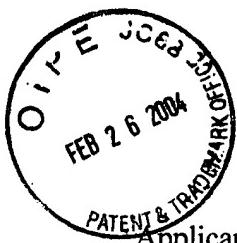
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Information Disclosure Statement (1 page)
PTO/SB/08A with 76 References Cited (5 pages)
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Respectfully submitted,

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Legal Assistant

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ge, et al. Attorney Docket: TSM03-0660
Filed: October 31, 2003 Examiner: TBD
Serial No.: 10/699,574 Art Unit: 2811
For: STRAINED SILICON STRUCTURE

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INFORMATION DISCLOSURE STATEMENT

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

Cite numbers 1-45 are newly cited prior art being filed under the waived requirement of 37 CFR 1.98 (a)(2)(i) dated July 11, 2003, therefore, copies of these U.S. patents are not included.

Respectfully submitted,

2/23/2004

Date


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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PTO/SB/08A (05-03)

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Application Number	10/699,574
Filing Date	October 31, 2003
First Named Inventor	Ge, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM03-0660

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-4,072,974	02-07-1978	Ipri	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
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<p style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p style="text-align: center;">(use as many sheets as necessary)</p>		Complete if Known	
		Application Number	10/699,574
		Filing Date	October 31, 2003
		First Named Inventor	Ge, et al.
		Art Unit	2811
		Examiner Name	TBD
Sheet	2	of	5
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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

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Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
	Country Code ³ - Number ⁴ - Kind Code ⁵ (<i>if known</i>)				
46	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

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Application Number	10/699,574
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	+ ²
	47	ISMAIL, K., et al., "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letter, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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	51	MIZUNO, T., et al., "Novel SOI p-Channel MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, Vol. 49, No. 1, (January 2002), pp. 7-14.	
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Application Number	10/699,574
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Art Unit	2811
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	+2
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